

## N-Channel 30 V (D-S) MOSFET

### DESCRIPTION

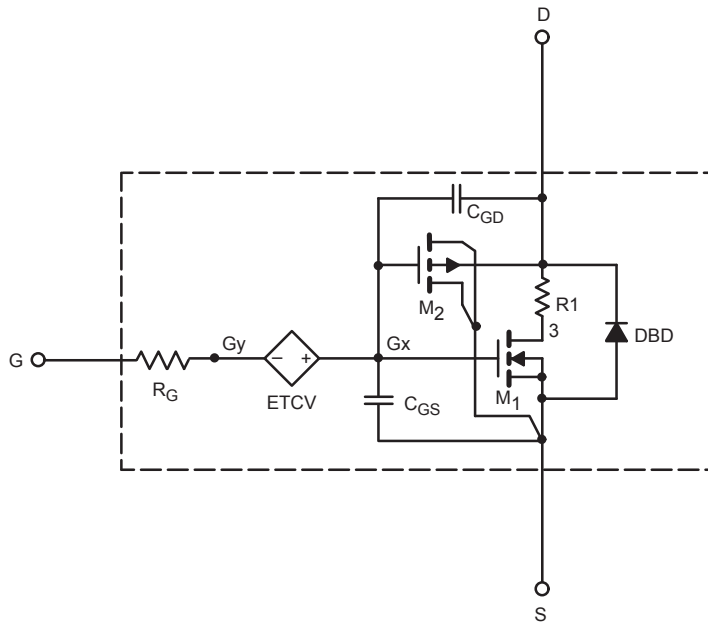
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



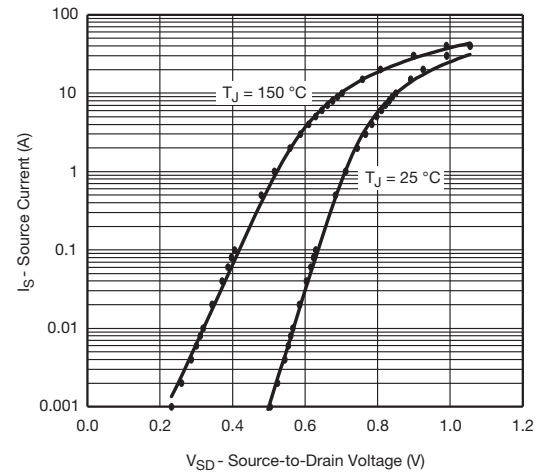
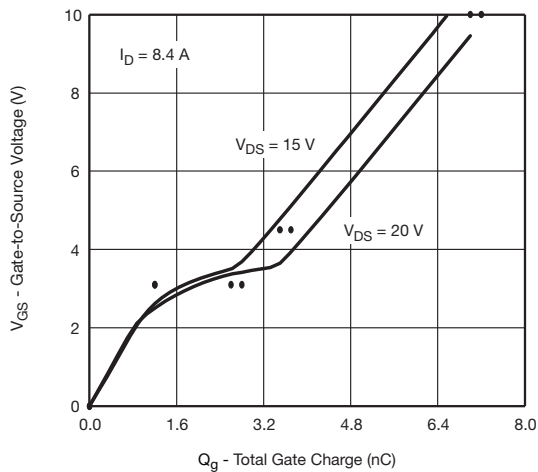
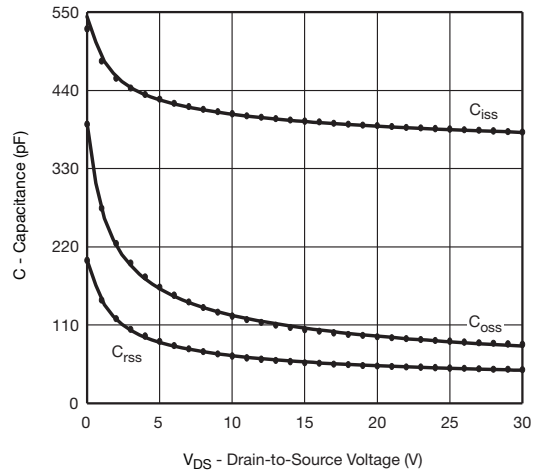
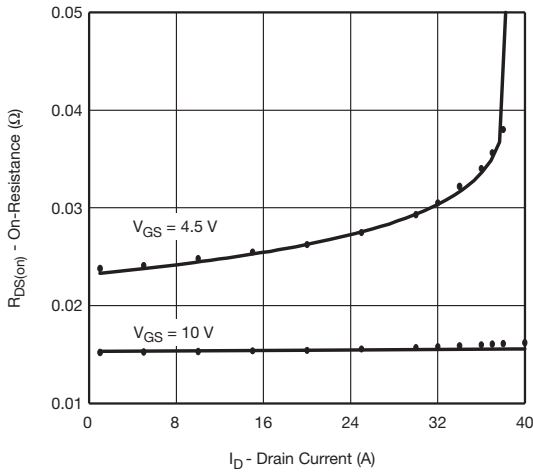
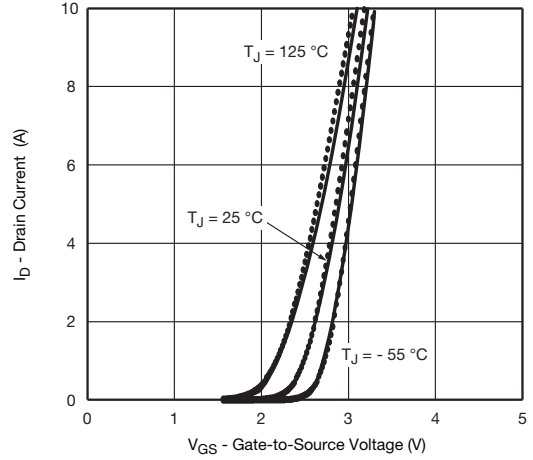
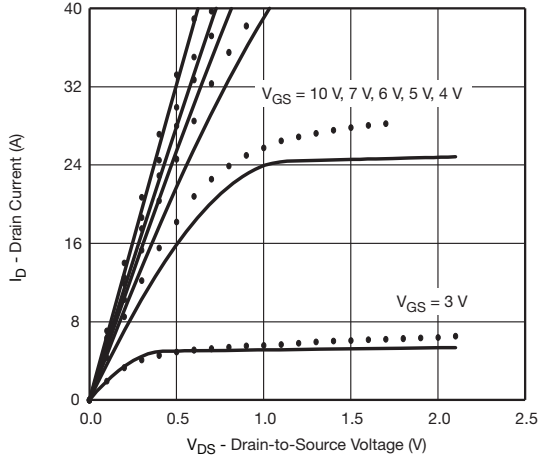
| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |              |   |                |               |               |
|---|--------------|---|----------------|---------------|---------------|
| PARAMETER   | SYMBOL       | TEST CONDITIONS   | SIMULATED DATA | MEASURED DATA | UNIT          |
| <b>Static</b>   |              |   |                |               |               |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$                   | 1.7            | -             | V             |
| Drain-Source On-State Resistance <sup>a</sup>                                   | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 8\text{ A}$                          | 0.016          | 0.016         | $\Omega$      |
|   |              | $V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$                         | 0.024          | 0.024         |               |
| Forward Transconductance <sup>a</sup>   | $g_{fs}$     | $V_{DS} = 10\text{ V}, I_D = 8\text{ A}$                          | 22             | 20            | S             |
| Body Diode Voltage  | $V_{SD}$     | $I_S = 5\text{ A}$  | 0.82           | 0.80          | V             |
| <b>Dynamic<sup>b</sup></b>  |              |   |                |               |               |
| Input Capacitance   | $C_{iss}$    | $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$     | 396            | 398           | $\mu\text{F}$ |
| Output Capacitance  | $C_{oss}$    |   | 106            | 104           |               |
| Reverse Transfer Capacitance  | $C_{rss}$    |   | 58             | 58            |               |
| Total Gate Charge   | $Q_g$        | $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 8.4\text{ A}$  | 6.7            | 7             | nC            |
| Gate-Source Charge  | $Q_{gs}$     | $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8.4\text{ A}$ | 3.3            | 3.6           |               |
| Gate-Source Charge  | $Q_{gs}$     |   | 1.1            | 1.1           |               |
| Gate-Drain Charge   | $Q_{gd}$     |   | 1.4            | 1.4           |               |

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted



### Note

Dots and squares represent measured data.



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